

RGCL60TK60

600V 30A Field Stop Trench IGBT

V _{CES}	600V
I _{C(100°C)}	18A
V _{CE(sat) (Typ.)}	1.4V@I _C =30A
P_D	54W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) Soft Switching
- 3) Pb free Lead Plating; RoHS Compliant

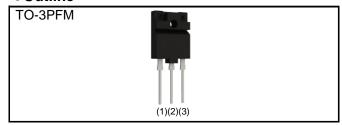
Applications

Partial Switching PFC

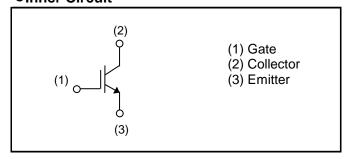
Discharge Circuit

Brake for Inverter

Outline



●Inner Circuit



Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Tuno	Tape Width (mm)	-
Type	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGCL60TK60

● Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V_{CES}	600	V
Gate - Emitter Voltage		V_{GES}	±30	V
Collector Current	T _C = 25°C	I _C	30	А
	T _C = 100°C	I _C	18	А
Pulsed Collector Current		I _{CP} *1	120	А
Power Dissipation	T _C = 25°C	P_{D}	54	W
	T _C = 100°C	P _D	27	W
Operating Junction Temperature		T _j	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

^{*1} Pulse width limited by T_{jmax.}

●Thermal Resistance

Parameter	Symbol	Values			Unit
raiametei		Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	2.77	°C/W

ullet IGBT Electrical Characteristics (at $T_j = 25$ °C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
raiametei	Syllibol	Conditions	Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_{C} = 10 \mu A, V_{GE} = 0 V$	600	-	1	V
Collector Cut - off Current	I _{CES}	$V_{CE} = 600V, V_{GE} = 0V$	ı	-	10	μΑ
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V$, $V_{CE} = 0V$	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 18.9 \text{mA}$	4.5	5.5	6.5	V
Collector - Emitter Saturation Voltage	V _{CE(sat)}	$I_C = 30A$, $V_{GE} = 15V$ $T_j = 25$ °C $T_j = 175$ °C	-	1.4 1.6	1.8 -	V

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Doromatar	Cymphal	Conditions	Values			Linit
Parameter	Symbol		Min.	Тур.	Max.	Unit
Input Capacitance	C _{ies}	V _{CE} = 30V	-	1600	-	
Output Capacitance	C _{oes}	$V_{GE} = 0V$	-	38	-	pF
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	29	-	
Total Gate Charge	Q_g	V _{CE} = 300V	-	68	-	
Gate - Emitter Charge	Q _{ge}	I _C = 30A	-	13	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	27	-	
Turn - on Delay Time	t _{d(on)}	$I_C = 30A, V_{CC} = 400V$	-	44	-	
Rise Time	t _r	$V_{GE} = 15V, R_G = 10\Omega$	-	27	-	no
Turn - off Delay Time	t _{d(off)}	T _j = 25°C	-	186	-	ns
Fall Time	t _f	Inductive Load	-	178	-	
Turn - on Switching Loss	E _{on}	*E _{on} includes diode	-	0.77	-	
Turn - off Switching Loss	E _{off}	reverse recovery	-	1.11	-	mJ
Turn - on Delay Time	t _{d(on)}	$I_C = 30A, V_{CC} = 400V$	-	40	-	
Rise Time	t _r	$V_{GE} = 15V, R_{G} = 10\Omega$	-	45	-	no
Turn - off Delay Time	t _{d(off)}	T _j = 175°C	-	207	-	ns
Fall Time	t _f	Inductive Load	-	272	-	
Turn - on Switching Loss	E _{on}	*E _{on} includes diode	-	0.97	-	m l
Turn - off Switching Loss	E _{off}	reverse recovery	-	1.54	-	mJ
		I _C = 120A, V _{CC} = 480V				
Reverse Bias Safe Operating Area	RBSOA	$V_P = 600V, V_{GE} = 15V$	FULL SQUARE			-
		$R_G = 60\Omega, T_j = 175^{\circ}C$				

Fig.1 Power Dissipation vs. Case Temperature

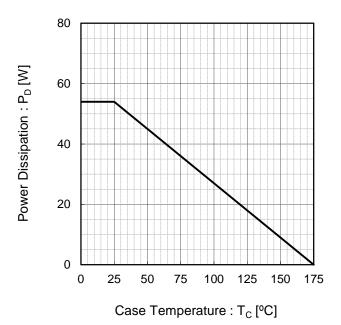


Fig.2 Collector Current vs. Case Temperature

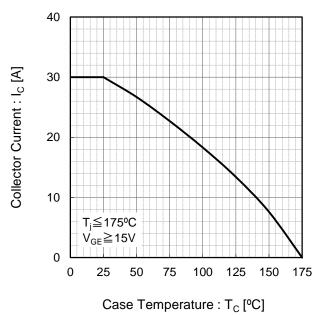
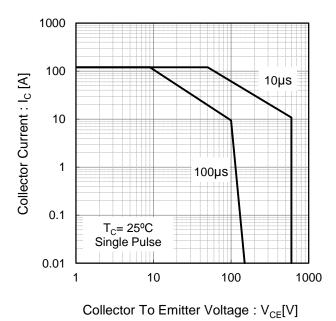


Fig.3 Forward Bias Safe Operating Area



Collector Current : I_c [A]

160
140
120
100
80
60
40
20
T_j≤175°C
V_{GE}=15V
0
0
200
400
600
800

Collector To Emitter Voltage : $V_{CE}[V]$

Fig.4 Reverse Bias Safe Operating Area

Fig.5 Typical Output Characteristics

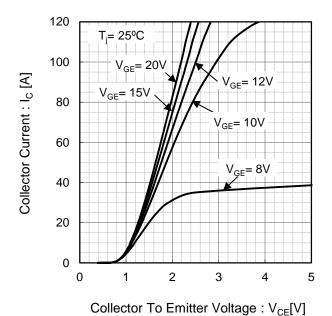
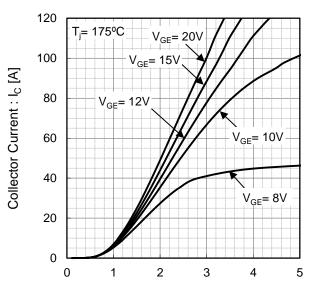


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage: V_{CE}[V]

Fig.7 Typical Transfer Characteristics

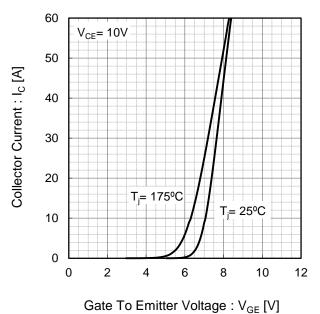
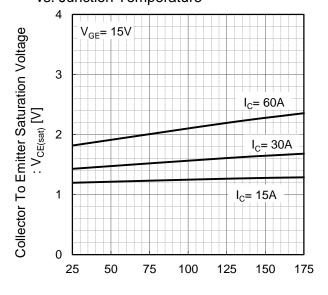
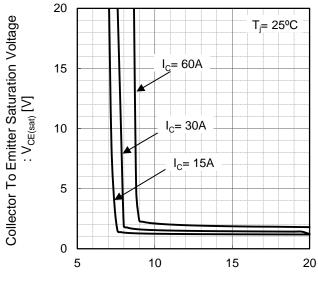


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



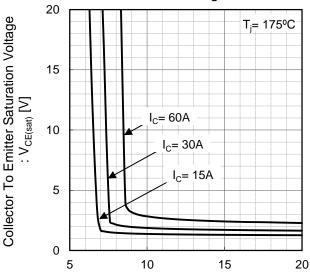
Junction Temperature : T_i [°C]

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

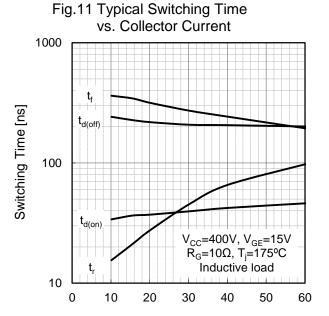


Gate To Emitter Voltage : V_{GE} [V]

Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage : V_{GE} [V]



Collector Current : I_C [A]

Fig.12 Typical Switching Time vs. Gate Resistance 1000 Switching Time [ns] t_{d(off)} 100 t_{d(on)} $V_{\rm CC}$ =400V, $I_{\rm C}$ =30A $V_{\rm GE}$ =15V, $T_{\rm j}$ =175°C Inductive load 10 0 10 20 30 40 50 Gate Resistance : $R_G[\Omega]$

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1 $\mathsf{E}_{\mathsf{off}}$ 0.1 V_{CC}=400V, V_{GE}=15V R_G=10Ω, T_j=175°C Inductive load 0.01 40 0 10 20 30 50 60 Collector Current : I_C [A]

vs. Gate Resistance 10 Switching Energy Losses [mJ] $\mathsf{E}_{\mathsf{off}}$ 1 E_{on} 0.1 V_{CC} =400V, I_{C} =30A V_{GE} =15V, T_{j} =175°C Inductive load 0.01 0 10 20 30 40 50 Gate Resistance : $R_G[\Omega]$

Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] 100 Coes Cres 10 f=1MHz $V_{GE}=0V$ T;=25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage : V_{CE}[V]

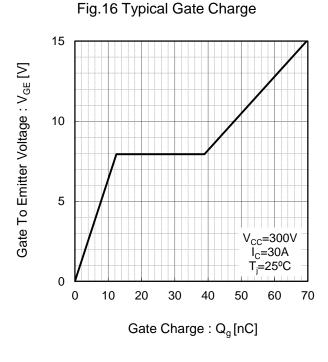
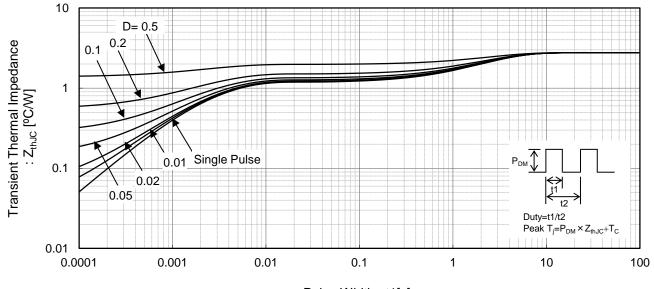


Fig.17 IGBT Transient Thermal Impedance



Pulse Width: t1[s]

●Inductive Load Switching Circuit and Waveform

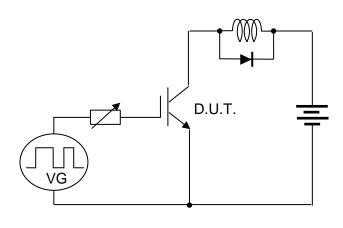


Fig.18 Inductive Load Circuit

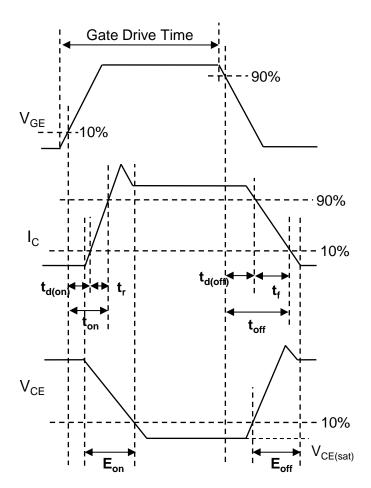


Fig.19 Inductive Load Waveform

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